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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Obsolete
Number of LABs/CLBs	1232
Number of Logic Elements/Cells	-
Total RAM Bits	-
Number of I/O	125
Number of Gates	8000
Voltage - Supply	4.5V ~ 5.5V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 85°C (TA)
Package / Case	160-BQFP
Supplier Device Package	160-PQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/microsemi/a1280a-1pqg160i

Product Plan

Device/Package	Speed Grade ¹			Application ¹			
	Std.	–1	–2	C	I	M	B
A1225A Device							
84-Pin Plastic Leaded Chip Carrier (PL)	✓	✓	✓	✓	✓	–	–
100-Pin Plastic Quad Flatpack (PQ)	✓	✓	✓	✓	✓	–	–
100-Pin Very Thin Quad Flatpack (VQ)	✓	✓	✓	✓	–	–	–
100-Pin Ceramic Pin Grid Array (PG)	✓	✓	✓	✓	–	–	–
A1240A Device							
84-Pin Plastic Leaded Chip Carrier (PL)	✓	✓	✓	✓	✓	–	–
132-Pin Ceramic Pin Grid Array (PG)	✓	✓	✓	✓	–	✓	✓
144-Pin Plastic Quad Flat Pack (PQ)	✓	✓	✓	✓	✓	–	–
176-Pin Thin (1.4 mm) Quad Flat Pack (TQ)	✓	✓	✓	✓	–	–	–
A1280A Device							
160-Pin Plastic Quad Flatpack (PQ)	✓	✓	✓	✓	✓	–	–
172-Pin Ceramic Quad Flatpack (CQ)	✓	✓	✓	✓	–	✓	✓
176-Pin Ceramic Pin Grid Array (PG)	✓	✓	✓	✓	–	✓	✓
176-Pin Thin (1.4 mm) Quad Flat Pack (TQ)	✓	✓	✓	✓	–	–	–

Notes:

1. Applications:
 C = Commercial
 I = Industrial
 M = Military
 B = MIL-STD-883

Availability:
 ✓ = Available
 P = Planned
 – = Not planned

Speed Grade:
 –1 = Approx. 15% faster than Std.
 –2 = Approx. 25% faster than Std.

2. Contact your Microsemi SoC Products Group sales representative for product availability.

Device Resources

Device Series	Logic Modules	Gates	User I/Os									
			PG176	PG132	PG100	PQ160	PQ144	PQ100	PL84	CQ172	TQ176	VQ100
A1225A	451	2,500	–	–	83	–	–	83	72	–	–	83
A1240A	684	4,000	–	104	–	–	104	–	72	–	104	–
A1280A	1,232	8,000	140	–	–	125	–	–	72	140	140	–

Contact your local Microsemi SoC Products Group representative for device availability:

<http://www.microsemi.com/soc/contact/default.aspx>.

Package Thermal Characteristics

The device junction to case thermal characteristic is θ_{jc} , and the junction to ambient air characteristic is θ_{ja} . The thermal characteristics for θ_{ja} are shown with two different air flow rates.

Maximum junction temperature is 150°C.

A sample calculation of the absolute maximum power dissipation allowed for a PQ160 package at commercial temperature and still air is as follows:

$$\frac{\text{Max. junction temp. (°C)} - \text{Max. ambient temp. (°C)}}{\theta_{ja} \text{ °C/W}} = \frac{150^{\circ}\text{C} - 70^{\circ}\text{C}}{33^{\circ}\text{C/W}} = 2.4 \text{ W}$$

EQ 1

Table 2-4 • Package Thermal Characteristics

Package Type*	Pin Count	θ_{jc}	θ_{ja} Still Air	θ_{ja} 300 ft./min.	Units
Ceramic Pin Grid Array	100	5	35	17	°C/W
	132	5	30	15	°C/W
	176	8	23	12	°C/W
Ceramic Quad Flatpack	172	8	25	15	°C/W
Plastic Quad Flatpack ¹	100	13	48	40	°C/W
	144	15	40	32	°C/W
	160	15	38	30	°C/W
Plastic Leaded Chip Carrier	84	12	37	28	°C/W
Very Thin Quad Flatpack	100	12	43	35	°C/W
Thin Quad Flatpack	176	15	32	25	°C/W

Notes: (Maximum Power in Still Air)

1. Maximum power dissipation values for PQFP packages are 1.9 W (PQ100), 2.3 W (PQ144), and 2.4 W (PQ160).
2. Maximum power dissipation for PLCC packages is 2.7 W.
3. Maximum power dissipation for VQFP packages is 2.3 W.
4. Maximum power dissipation for TQFP packages is 3.1 W.

Power Dissipation

$$P = [\text{ICC standby} + \text{ICC active}] * V_{CC} + \text{IOL} * \text{VOL} * N + \text{IOH} * (V_{CC} - \text{VOH}) * M$$

EQ 2

where:

ICC standby is the current flowing when no inputs or outputs are changing

ICC active is the current flowing due to CMOS switching.

IOL and IOH are TTL sink/source currents.

VOL and VOH are TTL level output voltages.

N is the number of outputs driving TTL loads to VOL.

M is the number of outputs driving TTL loads to VOH.

An accurate determination of N and M is problematical because their values depend on the family type, design details, and on the system I/O. The power can be divided into two components: static and active.

Static Power Component

Microsemi FPGAs have small static power components that result in lower power dissipation than PALs or PLDs. By integrating multiple PALs/PLDs into one FPGA, an even greater reduction in board-level power dissipation can be achieved.

The power due to standby current is typically a small component of the overall power. Standby power is calculated in Table 2-5 for commercial, worst case conditions.

Table 2-5 • Standby Power Calculation

ICC	VCC	Power
2 mA	5.25 V	10.5 mW

The static power dissipated by TTL loads depends on the number of outputs driving high or low and the DC load current. Again, this value is typically small. For instance, a 32-bit bus sinking 4 mA at 0.33 V will generate 42 mW with all outputs driving low, and 140 mW with all outputs driving high. The actual dissipation will average somewhere between as I/Os switch states with time.

Active Power Component

Power dissipation in CMOS devices is usually dominated by the active (dynamic) power dissipation. This component is frequency dependent, a function of the logic and the external I/O. Active power dissipation results from charging internal chip capacitances of the interconnect, unprogrammed antifuses, module inputs, and module outputs, plus external capacitance due to PC board traces and load device inputs.

An additional component of the active power dissipation is the totem-pole current in CMOS transistor pairs. The net effect can be associated with an equivalent capacitance that can be combined with frequency and voltage to represent active power dissipation.

Equivalent Capacitance

The power dissipated by a CMOS circuit can be expressed by EQ 3.

$$\text{Power } (\mu\text{W}) = C_{\text{EQ}} * V_{\text{CC}}^2 * F$$

EQ 3

Where:

C_{EQ} is the equivalent capacitance expressed in pF.

VCC is the power supply in volts.

F is the switching frequency in MHz.

Equivalent capacitance is calculated by measuring ICC active at a specified frequency and voltage for each circuit component of interest. Measurements have been made over a range of frequencies at a fixed value of VCC. Equivalent capacitance is frequency independent so that the results may be used over a wide range of operating conditions. Equivalent capacitance values are shown in Table 2-6.

Table 2-6 • CEQ Values for Microsemi FPGAs

Item	CEQ Value
Modules (C_{EQM})	5.8
Input Buffers (C_{EQI})	12.9
Output Buffers (C_{EQO})	23.8
Routed Array Clock Buffer Loads (C_{EQCR})	3.9

To calculate the active power dissipated from the complete design, the switching frequency of each part of the logic must be known. EQ 4 shows a piece-wise linear summation over all components.

$$\begin{aligned}
 \text{Power} = & VCC^2 * [(m * C_{EQM} * f_m)_{\text{modules}} + (n * C_{EQI} * f_n)_{\text{inputs}} \\
 & + (p * (C_{EQO} + C_L) * f_p)_{\text{outputs}} \\
 & + 0.5 * (q1 * C_{EQCR} * f_{q1})_{\text{routed_Clk1}} + (r1 * f_{q1})_{\text{routed_Clk1}} \\
 & + 0.5 * (q2 * C_{EQCR} * f_{q2})_{\text{routed_Clk2}} + (r2 * f_{q2})_{\text{routed_Clk2}}
 \end{aligned}$$

EQ 4

Where:

m = Number of logic modules switching at f_m

n = Number of input buffers switching at f_n

p = Number of output buffers switching at f_p

q1 = Number of clock loads on the first routed array clock

q2 = Number of clock loads on the second routed array clock

r_1 = Fixed capacitance due to first routed array clock

r_2 = Fixed capacitance due to second routed array clock

C_{EQM} = Equivalent capacitance of logic modules in pF

C_{EQI} = Equivalent capacitance of input buffers in pF

C_{EQO} = Equivalent capacitance of output buffers in pF

C_{EQCR} = Equivalent capacitance of routed array clock in pF

C_L = Output lead capacitance in pF

f_m = Average logic module switching rate in MHz

f_n = Average input buffer switching rate in MHz

f_p = Average output buffer switching rate in MHz

f_{q1} = Average first routed array clock rate in MHz

f_{q2} = Average second routed array clock rate in MHz

Table 2-7 • Fixed Capacitance Values for Microsemi FPGAs

Device Type	r_1 , routed_Clk1	r_2 , routed_Clk2
A1225A	106	106.0
A1240A	134	134.2
A1280A	168	167.8

Parameter Measurement

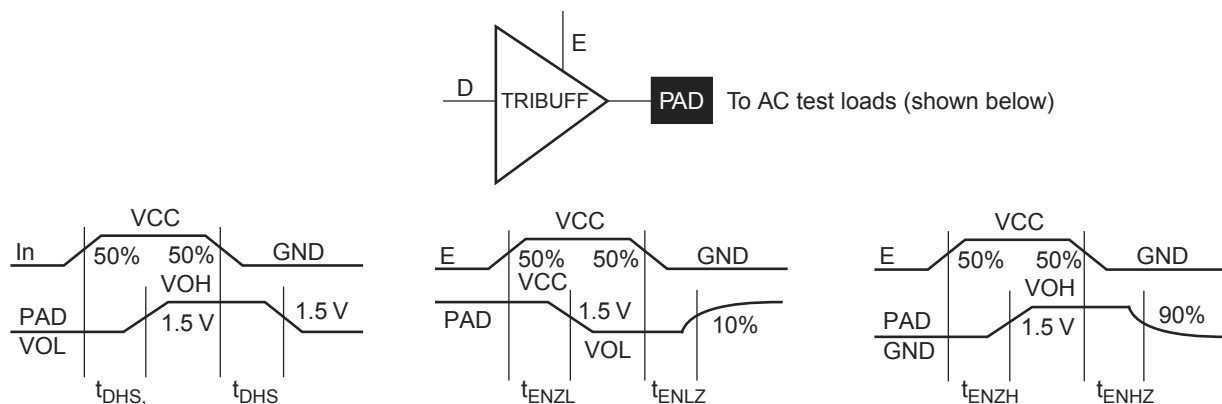


Figure 2-2 • Output Buffer Delays

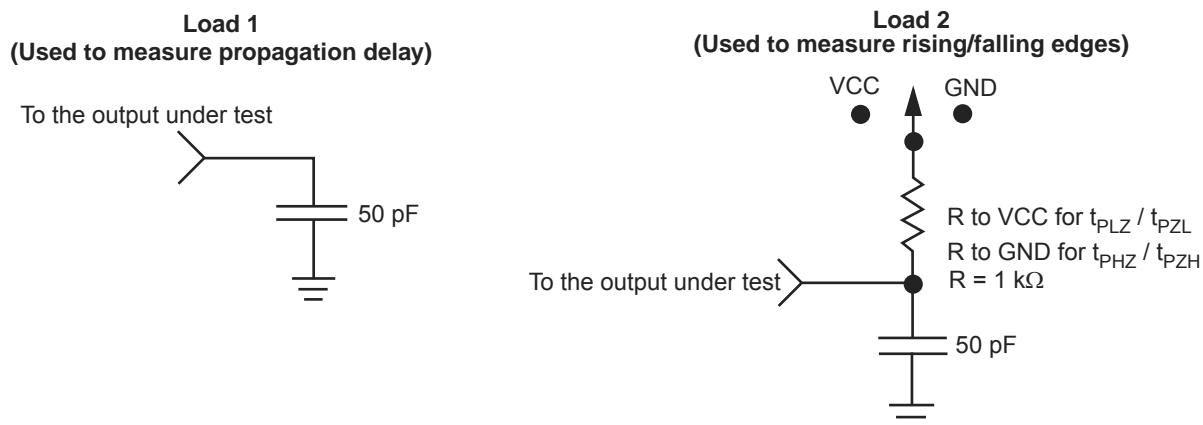


Figure 2-3 • AC Test Loads

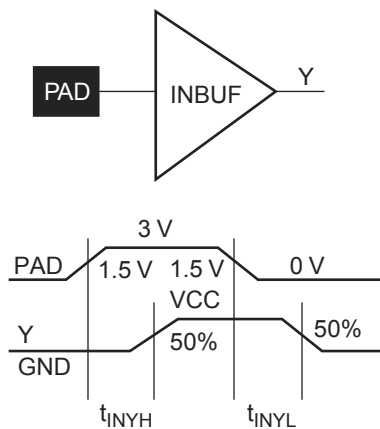


Figure 2-4 • Input Buffer Delays

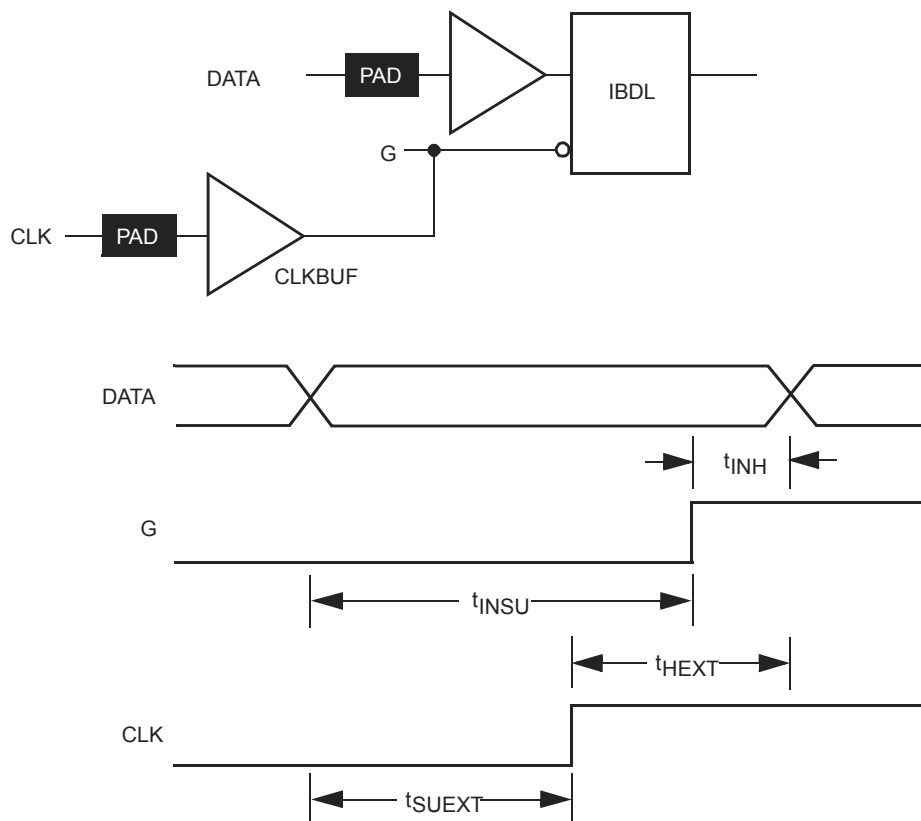


Figure 2-7 • Input Buffer Latches

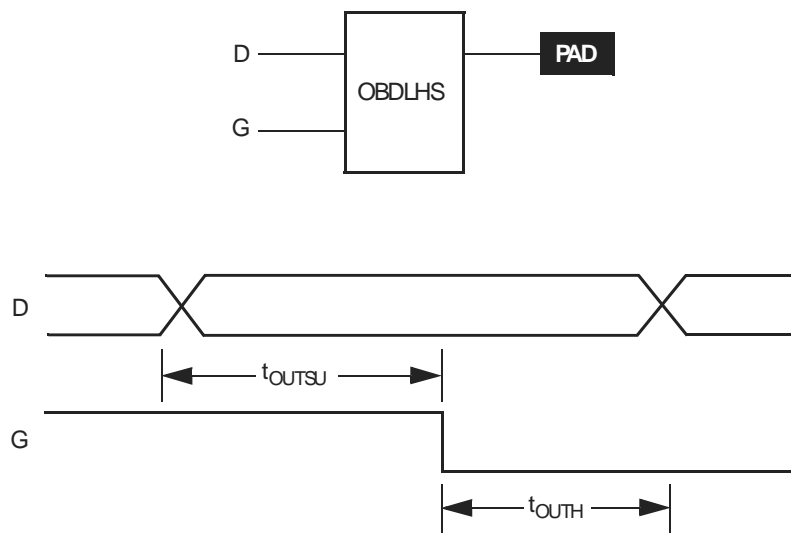


Figure 2-8 • Output Buffer Latches

A1225A Timing Characteristics

Table 2-12 • A1225A Worst-Case Commercial Conditions, VCC = 4.75 V, T_J = 70°C

Logic Module Propagation Delays ¹		–2 Speed ³		–1 Speed		Std. Speed		Units
Parameter/Description		Min.	Max.	Min.	Max.	Min.	Max.	
t _{PD1}	Single Module		3.8		4.3		5.0	ns
t _{CO}	Sequential Clock to Q		3.8		4.3		5.0	ns
t _{GO}	Latch G to Q		3.8		4.3		5.0	ns
t _{RS}	Flip-Flop (Latch) Reset to Q		3.8		4.3		5.0	ns
Predicted Routing Delays²								
t _{RD1}	FO = 1 Routing Delay		1.1		1.2		1.4	ns
t _{RD2}	FO = 2 Routing Delay		1.7		1.9		2.2	ns
t _{RD3}	FO = 3 Routing Delay		2.3		2.6		3.0	ns
t _{RD4}	FO = 4 Routing Delay		2.8		3.1		3.7	ns
t _{RD8}	FO = 8 Routing Delay		4.4		4.9		5.8	ns
Sequential Timing Characteristics^{3,4}								
t _{SUD}	Flip-Flop (Latch) Data Input Setup	0.4		0.4		0.5		ns
t _{HD}	Flip-Flop (Latch) Data Input Hold	0.0		0.0		0.0		ns
t _{SUENA}	Flip-Flop (Latch) Enable Setup	0.8		0.9		1.0		ns
t _{HENA}	Flip-Flop (Latch) Enable Hold	0.0		0.0		0.0		ns
t _{WCLKA}	Flip-Flop (Latch) Clock Active Pulse Width	4.5		5.0		6.0		ns
t _{WASYN}	Flip-Flop (Latch) Clock Asynchronous Pulse Width	4.5		5.0		6.0		ns
t _A	Flip-Flop Clock Input Period	9.4		11.0		13.0		ns
t _{INH}	Input Buffer Latch Hold	0.0		0.0		0.0		ns
t _{INSU}	Input Buffer Latch Setup	0.4		0.4		0.5		ns
t _{OUTH}	Output Buffer Latch Hold	0.0		0.0		0.0		ns
t _{OUTSU}	Output Buffer Latch Setup	0.4		0.4		0.5		ns
f _{MAX}	Flip-Flop (Latch) Clock Frequency		105.0		90.0		75.0	MHz

Notes:

1. For dual-module macros, use t_{PD1} + t_{RD1} + t_{PDn}, t_{CO} + t_{RD1} + t_{PDn}, or t_{PD1} + t_{RD1} + t_{SUD}—whichever is appropriate.
2. Routing delays are for typical designs across worst-case operating conditions. These parameters should be used for estimating device performance. Post-route timing analysis or simulation is required to determine actual worst-case performance. Post-route timing is based on actual routing delay measurements performed on the device prior to shipment.
3. Data applies to macros based on the S-module. Timing parameters for sequential macros constructed from C-modules can be obtained from the DirectTime Analyzer utility.
4. Setup and hold timing parameters for the Input Buffer Latch are defined with respect to the PAD and the D input. External setup/hold timing parameters must account for delay from an external PAD signal to the G inputs. Delay from an external PAD signal to the G input subtracts (adds) to the internal setup (hold) time.

A1240A Timing Characteristics

Table 2-15 • A1240A Worst-Case Commercial Conditions, VCC = 4.75 V, T_J = 70°C

Logic Module Propagation Delays ¹		–2 Speed ³		–1 Speed		Std. Speed		Units
Parameter/Description		Min.	Max.	Min.	Max.	Min.	Max.	
t _{PD1}	Single Module		3.8		4.3		5.0	ns
t _{CO}	Sequential Clock to Q		3.8		4.3		5.0	ns
t _{GO}	Latch G to Q		3.8		4.3		5.0	ns
t _{RS}	Flip-Flop (Latch) Reset to Q		3.8		4.3		5.0	ns
Predicted Routing Delays²								
t _{RD1}	FO = 1 Routing Delay		1.4		1.5		1.8	ns
t _{RD2}	FO = 2 Routing Delay		1.7		2.0		2.3	ns
t _{RD3}	FO = 3 Routing Delay		2.3		2.6		3.0	ns
t _{RD4}	FO = 4 Routing Delay		3.1		3.5		4.1	ns
t _{RD8}	FO = 8 Routing Delay		4.7		5.4		6.3	ns
Sequential Timing Characteristics^{3,4}								
t _{SUD}	Flip-Flop (Latch) Data Input Setup	0.4		0.4		0.5		ns
t _{HD}	Flip-Flop (Latch) Data Input Hold	0.0		0.0		0.0		ns
t _{SUENA}	Flip-Flop (Latch) Enable Setup	0.8		0.9		1.0		ns
t _{HENA}	Flip-Flop (Latch) Enable Hold	0.0		0.0		0.0		ns
t _{WCLKA}	Flip-Flop (Latch) Clock Active Pulse Width	4.5		6.0		6.5		ns
t _{WASYN}	Flip-Flop (Latch) Clock Asynchronous Pulse Width	4.5		6.0		6.5		ns
t _A	Flip-Flop Clock Input Period	9.8		12.0		15.0		ns
t _{INH}	Input Buffer Latch Hold	0.0		0.0		0.0		ns
t _{INSU}	Input Buffer Latch Setup	0.4		0.4		0.5		ns
t _{OUTH}	Output Buffer Latch Hold	0.0		0.0		0.0		ns
t _{OUTSU}	Output Buffer Latch Setup	0.4		0.4		0.5		ns
f _{MAX}	Flip-Flop (Latch) Clock Frequency		100.0		80.0		66.0	MHz

Notes:

1. For dual-module macros, use t_{PD1} + t_{RD1} + t_{PDn}, t_{CO} + t_{RD1} + t_{PDn}, or t_{PD1} + t_{RD1} + t_{SUD}—whichever is appropriate.
2. Routing delays are for typical designs across worst-case operating conditions. These parameters should be used for estimating device performance. Post-route timing analysis or simulation is required to determine actual worst-case performance. Post-route timing is based on actual routing delay measurements performed on the device prior to shipment.
3. Data applies to macros based on the S-module. Timing parameters for sequential macros constructed from C-modules can be obtained from the DirectTime Analyzer utility.
4. Setup and hold timing parameters for the Input Buffer Latch are defined with respect to the PAD and the D input. External setup/hold timing parameters must account for delay from an external PAD signal to the G inputs. Delay from an external PAD signal to the G input subtracts (adds) to the internal setup (hold) time.

Pin Descriptions

CLKA Clock A (Input)

TTL Clock input for clock distribution networks. The Clock input is buffered prior to clocking the logic modules. This pin can also be used as an I/O.

CLKB Clock B (Input)

TTL Clock input for clock distribution networks. The Clock input is buffered prior to clocking the logic modules. This pin can also be used as an I/O.

DCLK Diagnostic Clock (Input)

TTL Clock input for diagnostic probe and device programming. DCLK is active when the MODE pin is High. This pin functions as an I/O when the MODE pin is Low.

GND Ground

Low supply voltage.

I/O Input/Output (Input, Output)

The I/O pin functions as an input, output, three-state, or bidirectional buffer. Input and output levels are compatible with standard TTL and CMOS specifications. Unused I/O pins are automatically driven Low by the ALS software.

MODE Mode (Input)

The MODE pin controls the use of multifunction pins (DCLK, PRA, PRB, SDI). When the MODE pin is High, the special functions are active. When the MODE pin is Low, the pins function as I/Os. To provide Actionprobe capability, the MODE pin should be terminated to GND through a 10K resistor so that the MODE pin can be pulled High when required.

NC No Connection

This pin is not connected to circuitry within the device.

PRA Probe A (Output)

The Probe A pin is used to output data from any user-defined design node within the device. This independent diagnostic pin can be used in conjunction with the Probe B pin to allow real-time diagnostic output of any signal path within the device. The Probe A pin can be used as a user-defined I/O when debugging has been completed. The pin's probe capabilities can be permanently disabled to protect programmed design confidentiality. PRA is active when the MODE pin is High. This pin functions as an I/O when the MODE pin is Low.

PRB Probe B (Output)

The Probe B pin is used to output data from any user-defined design node within the device. This independent diagnostic pin can be used in conjunction with the Probe A pin to allow real-time diagnostic output of any signal path within the device. The Probe B pin can be used as a user-defined I/O when debugging has been completed. The pin's probe capabilities can be permanently disabled to protect programmed design confidentiality. PRB is active when the MODE pin is High. This pin functions as an I/O when the MODE pin is Low.

SDI Serial Data Input (Input)

Serial data input for diagnostic probe and device programming. SDI is active when the MODE pin is High. This pin functions as an I/O when the MODE pin is Low.

SDO Serial Data Output (Output)

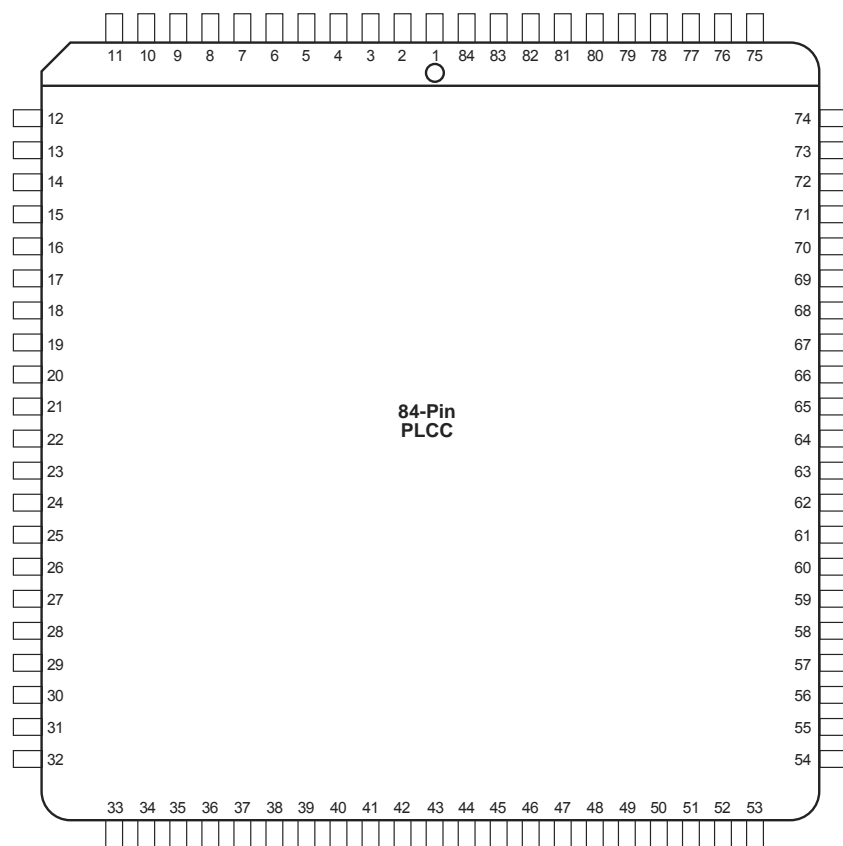
Serial data output for diagnostic probe. SDO is active when the MODE pin is High. This pin functions as an I/O when the MODE pin is Low.

VCC 5.0 V Supply Voltage

High supply voltage.

3 – Package Pin Assignments

PL84



Note

For Package Manufacturing and Environmental information, visit the Resource Center at <http://www.microsemi.com/soc/products/solutions/package/docs.aspx>.

PL84			
Pin Number	A1225A Function	A1240A Function	A1280A Function
2	CLKB, I/O	CLKB, I/O	CLKB, I/O
4	PRB, I/O	PRB, I/O	PRB, I/O
6	GND	GND	GND
10	DCLK, I/O	DCLK, I/O	DCLK, I/O
12	MODE	MODE	MODE
22	VCC	VCC	VCC
23	VCC	VCC	VCC
28	GND	GND	GND
43	VCC	VCC	VCC
49	GND	GND	GND
52	SDO	SDO	SDO
63	GND	GND	GND
64	VCC	VCC	VCC
65	VCC	VCC	VCC
70	GND	GND	GND
76	SDI, I/O	SDI, I/O	SDI, I/O
81	PRA, I/O	PRA, I/O	PRA, I/O
83	CLKA, I/O	CLKA, I/O	CLKA, I/O
84	VCC	VCC	VCC

Notes:

1. All unlisted pin numbers are user I/Os.
2. MODE pin should be terminated to GND through a 10K resistor to enable Actionprobe usage; otherwise it can be terminated directly to GND.

PQ144	
Pin Number	A1240A Function
2	MODE
9	GND
10	GND
11	GND
18	VCC
19	VCC
20	VCC
21	VCC
28	GND
29	GND
30	GND
44	GND
45	GND
46	GND
54	VCC
55	VCC
56	VCC
64	GND
65	GND
71	SDO
79	GND
80	GND
81	GND
88	GND

PQ144	
Pin Number	A1240A Function
89	VCC
90	VCC
91	VCC
92	VCC
93	VCC
100	GND
101	GND
102	GND
110	SDI, I/O
116	GND
117	GND
118	GND
123	PRA, I/O
125	CLKA, I/O
126	VCC
127	VCC
128	VCC
130	CLKB, I/O
132	PRB, I/O
136	GND
137	GND
138	GND
144	DCLK, I/O

Notes:

1. All unlisted pin numbers are user I/Os.
2. MODE pin should be terminated to GND through a 10K resistor to enable Actionprobe usage; otherwise it can be terminated directly to GND.

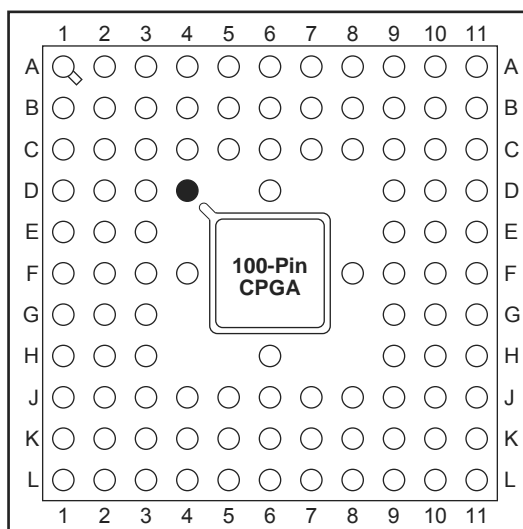
CQ172	
Pin Number	A1280A Function
1	MODE
7	GND
12	VCC
17	GND
22	GND
23	VCC
24	VCC
27	VCC
32	GND
37	GND
50	VCC
55	GND
65	GND
66	VCC
75	GND
80	VCC
85	SDO
98	GND
103	GND
106	GND

CQ172	
Pin Number	A1280A Function
107	VCC
108	GND
109	VCC
110	VCC
113	VCC
118	GND
123	GND
131	SDI, I/O
136	VCC
141	GND
148	PRA, I/O
150	CLKA, I/O
151	VCC
152	GND
154	CLKB, I/O
156	PRB, I/O
161	GND
166	VCC
171	DCLK, I/O

Notes:

1. All unlisted pin numbers are user I/Os.
2. MODE pin should be terminated to GND through a 10K resistor to enable Actionprobe usage; otherwise it can be terminated directly to GND.

PG100



● Orientation Pin

Note

For Package Manufacturing and Environmental information, visit the Resource Center at <http://www.microsemi.com/soc/products/solutions/package/docs.aspx>

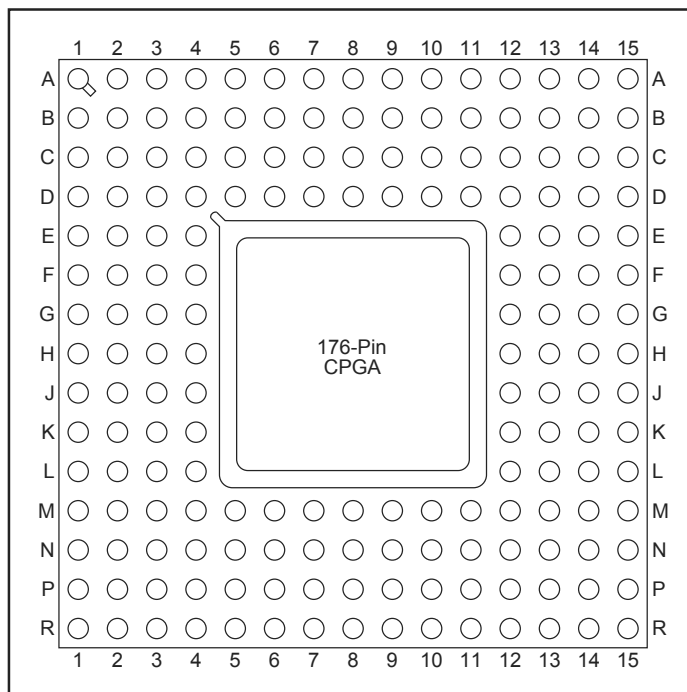
PG132	
Pin Number	A1240A Function
A1	MODE
B5	GND
B6	CLKB, I/O
B7	CLKA, I/O
B8	PRA, I/O
B9	GND
B12	SDI, I/O
C3	DCLK, I/O
C5	GND
C6	PRB, I/O
C7	VCC
C9	GND
D7	VCC
E3	GND
E11	GND
E12	GND
F4	GND
G2	VCC

PG132	
Pin Number	A1240A Function
G3	VCC
G4	VCC
G10	VCC
G11	VCC
G12	VCC
G13	VCC
H13	GND
J2	GND
J3	GND
J11	GND
K7	VCC
K12	GND
L5	GND
L7	VCC
L9	GND
M9	GND
N12	SDO

Notes:

1. All unlisted pin numbers are user I/Os.
2. MODE pin should be terminated to GND through a 10K resistor to enable Actionprobe usage; otherwise it can be terminated directly to GND.

PG176



Note

For Package Manufacturing and Environmental information, visit the Resource Center at <http://www.microsemi.com/soc/products/solutions/package/docs.aspx>

4 – Datasheet Information

List of Changes

The following table lists critical changes that were made in each version of the datasheet.

Revision	Changes	Page
Revision 8 (January 2012)	The ACT 2 datasheet was formatted newly in the style used for current datasheets. The same information is present (other than noted in the list of changes for this revision) but divided into chapters.	N/A
	Package names used in Table 1 • ACT 2 Product Family Profile and throughout the document were revised to match standards given in <i>Package Mechanical Drawings</i> (SAR 27395).	I
	The description for SDO pins had earlier been removed from the datasheet and has now been included again, in the "Pin Descriptions" section (SAR 35819).	2-21
	SDO pin numbers had earlier been removed from package pin assignment tables in the datasheet, and have now been restored to the pin tables (SAR 35819).	3-2
Revision 7 (June 2006)	The "Ordering Information" section was revised to include RoHS information.	II
Revision 6 (December 2000)	In the "PG176" package, pin A3 was incorrectly assigned as CLKA, I/O. A3 is a user I/O. Pin A9 is CLKA, I/O.	3-21

Datasheet Categories

Categories

In order to provide the latest information to designers, some datasheet parameters are published before data has been fully characterized from silicon devices. The data provided for a given device is designated as either "Product Brief," "Advance," "Preliminary," or "Production." The definitions of these categories are as follows:

Product Brief

The product brief is a summarized version of a datasheet (advance or production) and contains general product information. This document gives an overview of specific device and family information.

Advance

This version contains initial estimated information based on simulation, other products, devices, or speed grades. This information can be used as estimates, but not for production. This label only applies to the DC and Switching Characteristics chapter of the datasheet and will only be used when the data has not been fully characterized.

Preliminary

The datasheet contains information based on simulation and/or initial characterization. The information is believed to be correct, but changes are possible.

Production

This version contains information that is considered to be final.

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